

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the Specification (continued).

Please amend the ABSTRACT OF THE DISCLOSURE as set forth below.

Line 2, after "equivalent" please delete **[in thickness]**; same line, after "to" please insert

~~—~~ **a layer of silicon dioxide having a thickness of** --.

Line 3, after "or less" please delete **[of silicon dioxide]**.

Line 5, after "source and drain" please delete **[junctions]** and substitute therefor –
regions --.

Line 7, after "source and drain" please delete **[junctions]** and substitute therefor –
regions --.

In the Claims

Please amend claim 49 as set forth below.

49. (Amended) A method for making a non-volatile semiconductor device comprising:

forming a multilayer gate dielectric having a charge storage layer **[with alterable charge storage properties by application of an electric field,]** and **being** **[having a dielectric thickness]** **dielectrically** equivalent to **[that of]** a layer of silicon dioxide **having a thickness** that is less than **[about 170]** **200** angstroms;

forming a gate comprising polycrystalline silicon of first conductivity type on said gate dielectric; and

forming source and drain regions separated by a channel region in a semiconductor substrate, said source and drain regions having a second conductivity type different from said first **conductivity** **[dielectric]** type.